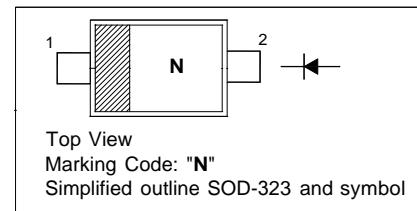


Silicon Epitaxial Schottky Barrier Diode

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

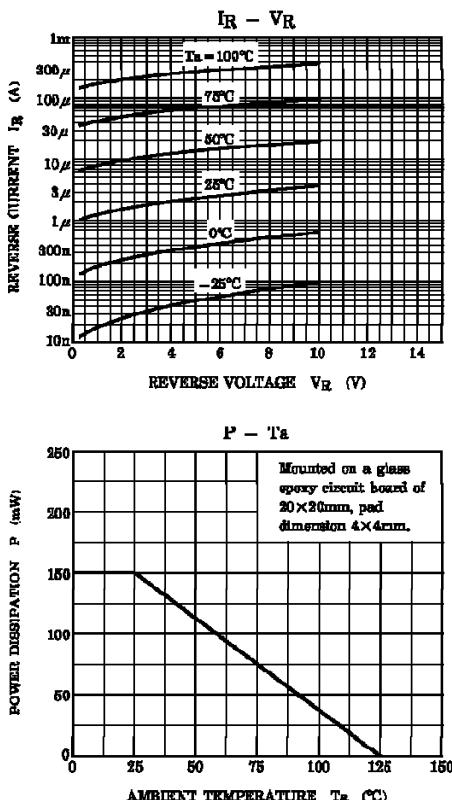
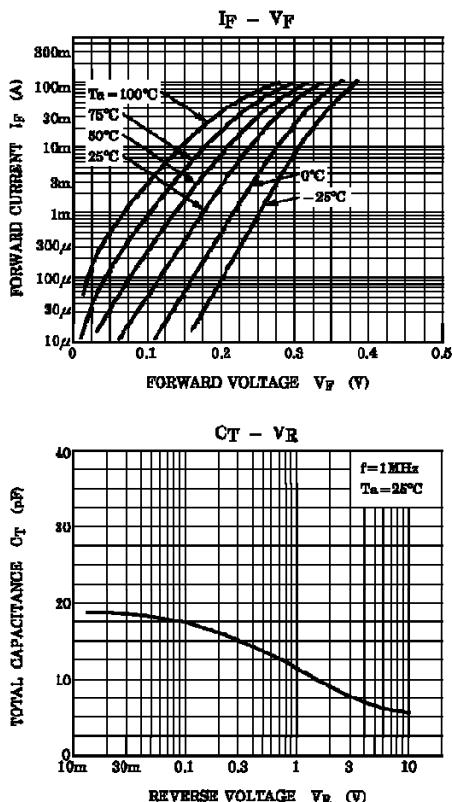


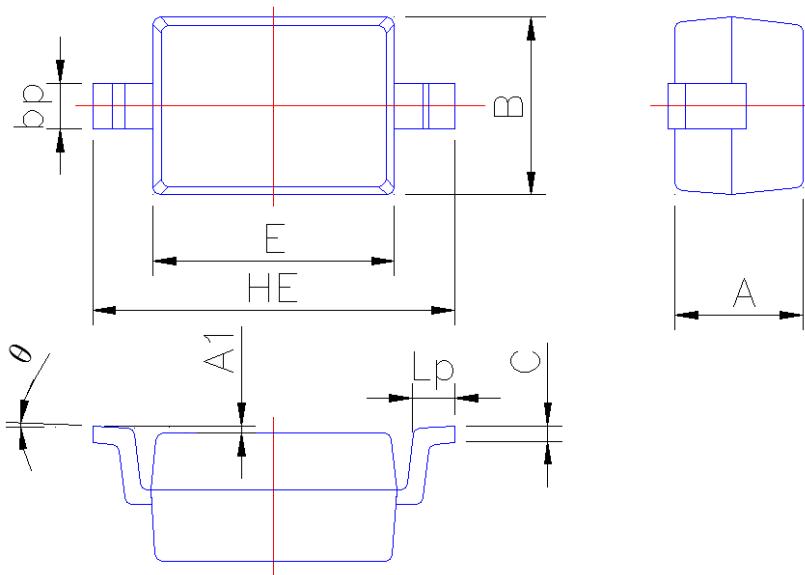
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	200	mA
Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	150	mW
Operating Temperature Range	T_{opr}	- 40 to + 100	°C
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 5 \text{ mA}$ at $I_F = 100 \text{ mA}$	V_F	0.3 0.5	V
Reverse Current at $V_R = 10 \text{ V}$	I_R	20	µA
Total Capacitance at $V_R = 0$, $f = 1 \text{ MHz}$	C_T	40	pF



PACKAGE OUTLINE
Plastic surface mounted package; 2 leads
SOD-323


Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°